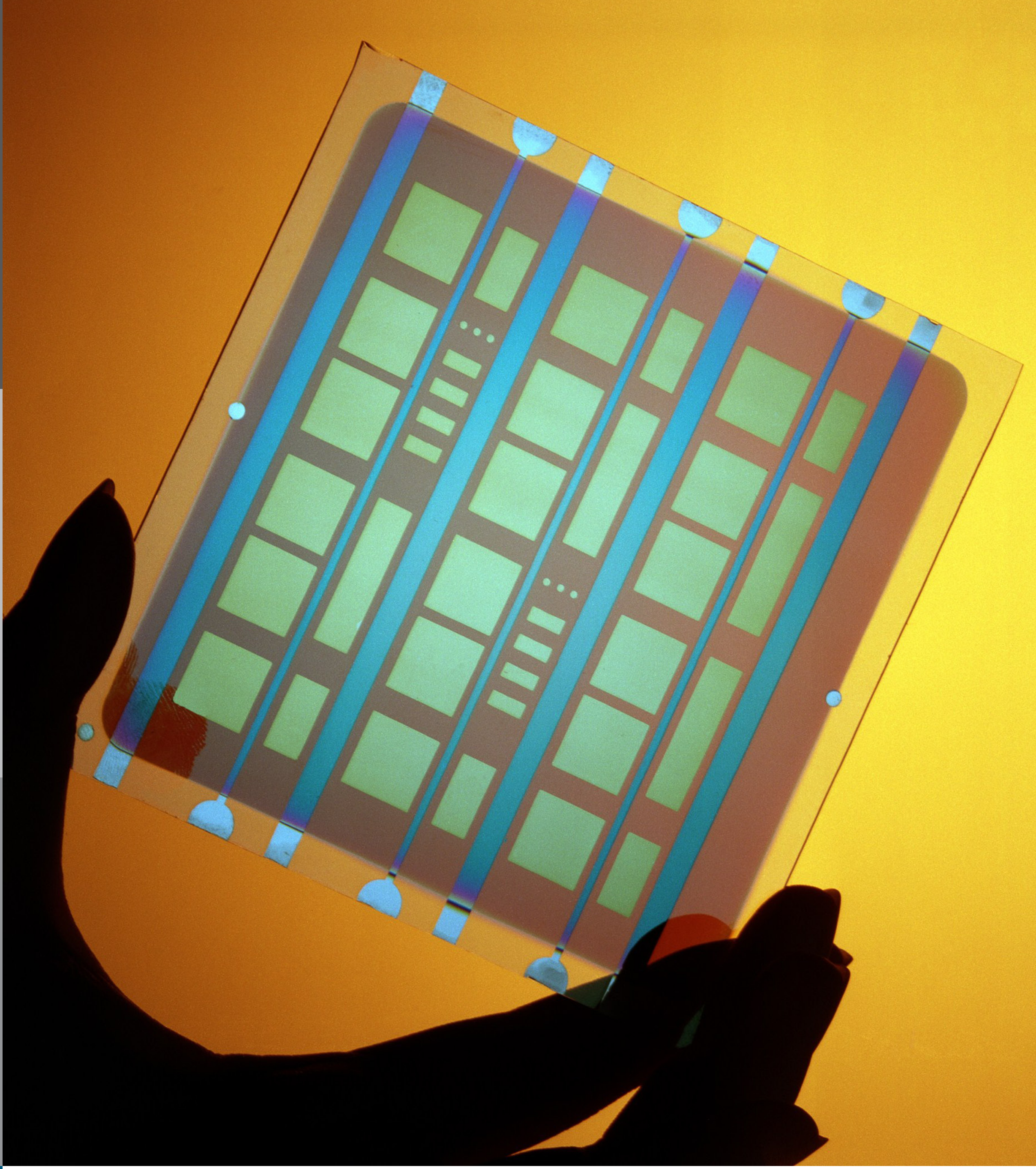

Electron Spin Resonance Investigation of Semiconductor Materials for Application in Thin-Film Silicon Solar Cells

Lihong Xiao

Mitglied der Helmholtz-Gemeinschaft

JÜLICH
FORSCHUNGSZENTRUM

Forschungszentrum Jülich GmbH
Institute for Energy and Climate Research (IEK)
Photovoltaics (IEK-5)

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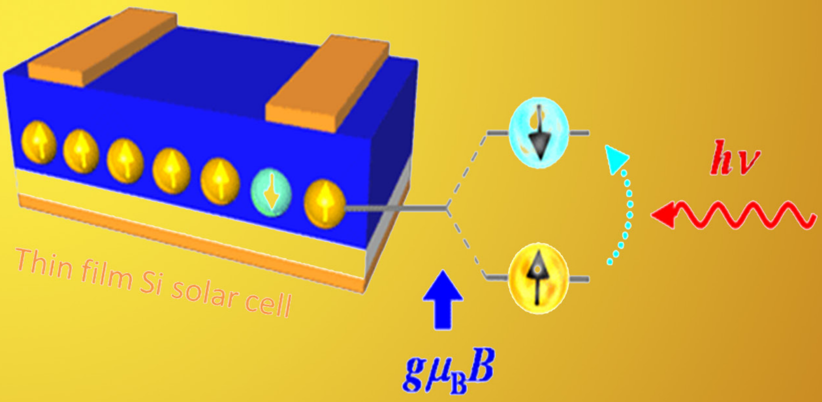

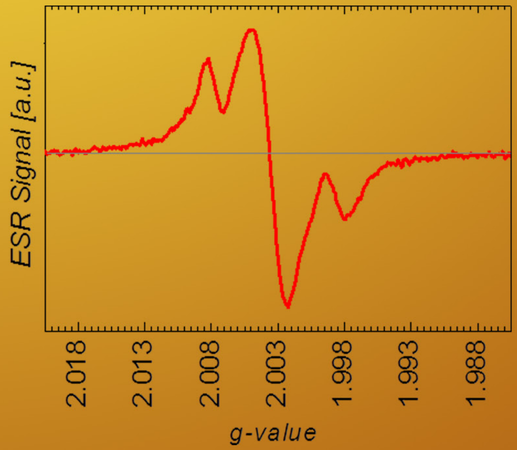

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